

Serial N . 09/843,783
Art Unit: 2823

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flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

REMARKS

Applicant again amended claims 1 and 15 for additional clarity, although Applicant respectfully traverses the Examiner's objections to claims 1-15. (Comment 8)

Applicant respectfully requests deferral of the corrected drawings until after indication of allowable subject matter. (Comment 11)

Rejection Under 35 USC 103

To the extent any art rejection continues to be applied against claims 1 and 15, twice amended, reconsideration is respectfully requested.

Neither Czubatyj ('690) nor Furukawa ('614), either singly or in combination, teaches, discloses or suggests "at a substantially constant flow rate for the dopant precursor while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases," let alone in combination with the remaining elements of Applicant's invention (claims 1, 15, twice amended).

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See also page 7, lines 6-11 of the instant application as filed, for a recitation of an unexpected result. (Comments 1-10)

Entry and allowance are solicited.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. This appendix is captioned "Version with Markings to Show Changes Made".

Respectfully submitted,
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Attachment: Appendix - Version with Markings to Show Changes Made

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- 4 -

Application Serial N . 09/843,783

Page 1 f1

VERSION WITH MARKINGS TO SHOW CHANGES MADE**In the Claims:****Kindly amend independent claims 1 and 15 as follows:**

1. (Twice Amended) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate [according to a relationship of the precursors as shown in Fig. 2] at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

15. (Twice Amended) A method of growing a film without sharp pressure transitions, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate [according to a relationship of the precursors as shown in Fig. 2] at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

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